REMARKS/ARGUMENT

The Examiner's indication that claim 2 would be allowable in independent form has been noted with appreciation. The applicant is satisfied with claims of that scope and has therefore combined claims 1 and 2. As a result of this amendment, it is respectfully submitted that all claims are now in condition to be allowed and the early issuance of a Notice of Allowance is respectfully solicited.

Respectfully submitted,

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APPENDIX A
Version With Markings To Show Changes Made
37 C.F.R. § 1.121(b)(1)(iii) AND (c)(1)(ii)

CLAIMS:

1. An electric device comprising:

a substrate;

a lower electrode layer on the substrate and comprising a material capable of reactive-ion etching with a fluorine-based gas which is at least one element selected from the group consisting of Si, Mo, W, B, C, S and Ta; and

an upper electrode layer on the lower electrode layer and comprising a material capable of reactive-ion etching with a chlorine-based gas, wherein said upper electrode comprises Al.

3. An electronic device according to Claim [2] 1, wherein the lower electrode has a thickness of about 0.5 nm to 1000 nm.

APPENDIX B
"Clean" Version Without Amended/New Indications
37 C.F.R. § 1.121(b)(1)(iii) AND (c)(3)

CLAIMS:

1. An electric device comprising:

a substrate;

a lower electrode layer on the substrate and comprising a material capable of reactive-ion etching with a fluorine-based gas which is at least one element selected from the group consisting of Si, Mo, W, B, C, S and Ta; and

an upper electrode layer on the lower electrode layer and comprising a material capable of reactive-ion etching with a chlorine-based gas, wherein said upper electrode comprises Al.

3. An electronic device according to Claim 1, wherein the lower electrode has a thickness of about 0.5 nm to 1000 nm.

4. An electronic device according to Claim 3, wherein the support comprises a piezoelectric material.

5. An electronic device according to Claim 4, wherein the lower electrode has a thickness of about 5-500 nm.

6. An electronic device according to Claim 5, wherein the substrate is selected from the group consisting of a single crystal substrate, single crystal film, triaxial orientation film and uniaxial orientation film.

7. An electronic device according to Claim 1, wherein the lower electrode has a thickness of about 0.5 nm to 1000 nm.

8. An electronic device according to Claim 1, wherein the support comprises a piezoelectric material.

9. An electronic device according to Claim 1, wherein the substrate is selected from the group consisting of a single crystal substrate, single crystal film, triaxial orientation film and uniaxial orientation film.